Abstracts

20 GHz High Power High Efficiency HEMT Module

C.H. Chen, H.C. Yen, K. Tan, L. Callejo, G. Onak, D.C. Streit, P.H. Liu and J.M. Schellenberg. "20 GHz High Power High Efficiency HEMT Module." 1993 MTT-S International Microwave Symposium Digest 93.3 (1993 Vol. III [MWSYM]): 1377-1380.

We are reporting the development of a high gain, high power and high efficiency K-band MIC power module employing four 1.6 mm pseudomorphic InGaAs HEMT devices. Power output of 3.2 Watts with 10 dB gain and 35% power-added efficiency at 3 dB compression was obtained at 20 GHz. The 1 dB bandwidth is 1.7 GHz.

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